

DESCRIPTION:

The JST04W-600SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST04W-600SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. Package SOT-223-2L is RoHS compliant.

MAIN FEATURES

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
T_{stg}	Storage junction temperature range	-40-150	
T_j	Operating junction temperature range	-40-125	
V_{DRM}	Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	600	V
V_{RRM}	Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	600	V
$I_{T(RMS)}$	RMS on-state current ($T_c = 102^\circ\text{C}$)	1	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	25	A
	Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)	27.5	
I^2t	I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	3.1	A^2s
di/dt	Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	100	A/s
I_{GM}	Peak gate current ($t_p=20\text{ }\mu\text{s}$, $T_j=125^\circ\text{C}$)	2	A
$P_{G(AV)}$	Average gate power dissipation ($T_j=125^\circ\text{C}$)	0.1	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	3	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

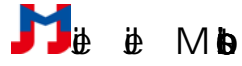
I_{GT}	V_{GT}	$R_{DS(on)}$	$R_{\theta(jc)}$	$R_{\theta(ja)}$	θ_{JA}
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1 1	

ORDERING INFORMATION

	<u>J</u>	<u>ST</u>	<u>04</u>	<u>W</u>	<u>-600</u>	<u>SW</u>
JieJie Microelectronics Co., Ltd.	Triacs	$I_T(RMS):1A$				
			W:SOT-223-2L			SW:IGT1-3 10mA
					600:VDRM/VRRM	600V

MARKING

<p>04W6SW XXX XXX</p>	<p><u>XXX XXX</u></p> <p>— LOT NO.</p>
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Ⓔ : Maximum power dissipation versus RMS on-state current

Ⓔ RMS on-state current versus case temperature

Relative variations of gate trigger current, holding current and latching current versus junction temperature

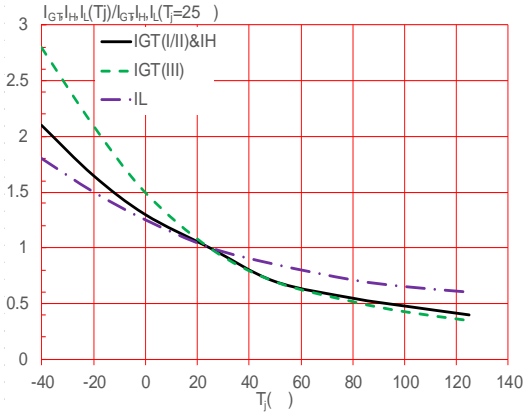
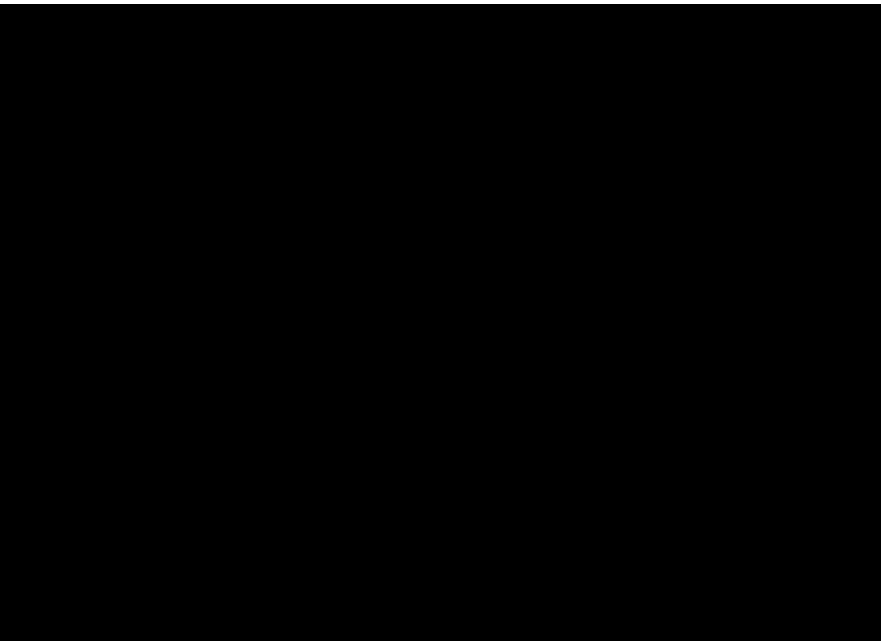




FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5./7 ()-13.0 (3e7 (Me16 (no



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ORDERING INFORMATION

 V _{MI} Y _{MI} Y _{MI}	G A)		<input type="text"/>
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DELIVERY MODE

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W						
E D0()Tj7.895 80 ie P2()Tj 5.002 Tc -5Tc 0 Tc5-2.895 -2.						

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